



INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

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MAY 06 2002

Docket Number (Optional)	Application Number
GS 174	10/039,284
Applicant(s)	
Richard A. Blanchard et al.	
Filing Date	Group Art Unit
12/31/01	2811

U.S. PATENT DOCUMENTS

**COPY OF PAPER
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FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (*Including Author, Title, Date, Pertinent Pages, Etc.*)

G. Deboy et al., "A new generation of high voltage MOSFETs breaks the limit line of silicon," Int'l Electron Devices Meeting, December 1998, 26.2.1, pp. 683-685.

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EXAMINER

PHAT X. CAO

DATE CONSIDERED

9/8/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.